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Retraction

RETRACTED: Zhang et al. Effects of Current Filaments on IGBT Avalanche Robustness: A Simulation Study. *Electronics* 2024, *13*, 2347

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The *Electronics* Editorial Office retracts the article "Effects of Current Filaments on IGBT Avalanche Robustness: A Simulation Study" [1], cited above.

Following publication, the authors contacted the Editorial Office regarding errors identified in the simulation model and analysis presented in the article [1].

Adhering to our standard procedure, an investigation was conducted by the Editorial Board that confirmed that the simulation presented in this paper is incorrect due to the use of incorrect material parameters: Silicon Carbide (SiC) parameters were used, instead of Silicon (Si). Consequently, the conclusions drawn from this simulation are invalid and cannot be relied upon. As a result, the Editorial Office, Editorial Board, and the authors have concluded that this error undermines the validity and accuracy of the findings, and have decided to retract this article [1] as per MDPI's retraction policy (https://www.mdpi.com/ethics#_bookmark30).

This retraction was approved by the Editor-in-Chief of the journal *Electronics*.

The authors agree to this retraction.

Reference

1. Zhang, J.; Luo, H.; Wu, H.; Zheng, B.; Chen, X.; Zhang, G.; French, P.; Wang, S. RETRACTED: Effects of Current Filaments on IGBT Avalanche Robustness: A Simulation Study. *Electronics* **2024**, *13*, 2347. [CrossRef]

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